SN74LVC1GU04-Q1 Automotive Single Unbuffered Inverter

1 Features

- AEC-Q100 qualified for automotive applications:
  - Device temperature grade 1: -40°C to +125°C
- Operating range from 1.65V to 5.5V
- 5.5V tolerant input pins
- Supports standard pinouts
- Latch-up performance exceeds 100mA per JESD 78

2 Applications

- Body control modules
- Engine control modules
- Infotainment systems
- Telematics

3 Description

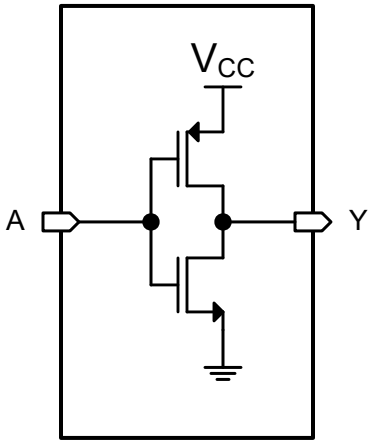
The SN74LVC1GU04-Q1 is a single channel unbuffered CMOS inverter.

Unbuffered inverters contain a single CMOS inverter stage and can be operated both in standard digital switching applications and in the analog linear region. While primarily specified for digital operation, the unbuffered architecture supports potential analog applications such as crystal oscillator circuits or linear amplification.

Package Information

PART NUMBER	PACKAGE(1)	PACKAGE SIZE(2)	BODY SIZE (NOM)(3)
SN74LVC1GU04-Q1	DCK (SC-70, 5)	2mm × 2.1mm	2mm × 1.25mm

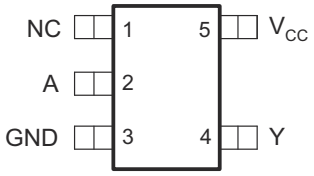
(1) For all available packages, see the orderable addendum at the end of the data sheet.
(2) The package size (length × width) is a nominal value and includes pins, where applicable.
(3) The body size (length × width) is a nominal value and does not include pins.



Functional Diagram

Table of Contents

4 Pin Configuration and Functions



NC – no internal connection

For package dimensions see the mechanical drawings at the end of the data sheet.

Figure 4-1. DCK 5-pin SC-70 Top View

Table 4-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
A	2	I	Signal input
GND	3	G	Ground
NC	1	—	No internal connection
V_{CC}	5	P	Supply voltage
Y	4	O	Signal output

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	6.5	V
V_I	Input voltage range(2)		-0.5	6.5	V
V_O	Output voltage range(2)		-0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0V		-50	mA
I_{OK}	Output clamp current	V_O < 0V		-50	mA
I_O	Continuous output current			±50	mA
I_O	Continuous output current through V_{CC} or GND			±100	mA
T_J	Junction temperature		-65	150	°C
T_{stg}	Storage temperature		-65	150	°C

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2(1)	±2000	V
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1000	

(1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

Specifications	Description	Condition	MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	1.65	5.5	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	(High or low state)	0	V_{CC}	V
V_{IH}	High-level input voltage	V_{CC} = 1.65V to 1.95V	0.65x Vcc		V
		V_{CC} = 2.3V to 2.7V	1.7		
		V_{CC} = 3.0V to 3.6V	2		
		V_{CC} = 4.5V to 5.5V	0.7x Vcc		
V_{IL}	Low-Level input voltage	V_{CC} = 1.65V to 1.95V		0.35x Vcc	V
		V_{CC} = 2.3V to 2.7V		0.7	
		V_{CC} = 3.0V to 3.6V		0.8	
		V_{CC} = 4.5V to 5.5V		0.3x Vcc	
I_{OH}	High-level output current	V_{CC} = 1.65V		-4	mA
		V_{CC} = 2.3V		-8	
		V_{CC} = 3.0V		-16	
				-24	
		V_{CC} = 4.5V		-32	

over operating free-air temperature range (unless otherwise noted)

Specifications	Description	Condition	MIN	MAX	UNIT
I_{OL}	Low-level output current	V_{CC} = 1.65V		4	mA
		V_{CC} = 2.3V		8	
		V_{CC} = 3.0V		16	
				24	
		V_{CC} = 4.5V		32	
Δt/Δv	Input transition rise or fall rate	V_{cc} = 1.1V to 5.5V		20	ns/V
T_A	Operating free-air temperature		-40	125	°C

5.4 Thermal Information

PACKAGE	PINS	THERMAL METRIC(1)						UNIT
		$R_{\theta JA}$	$R_{\theta JC(top)}$	$R_{\theta JB}$	Ψ_{JT}	Ψ_{JB}	$R_{\theta JC(bot)}$	
DCK (SOT-SC70, 5)	5	276.1	178.9	70.9	47	69.3	-	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application note.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	-40°C to 125°C			UNIT
			MIN	TYP	MAX	
V_{OH}	I_{OH}= –100µA	1.65V to 5.5V	V_{CC} - 0.1			V
V_{OH}	I_{OH}= –4mA	1.65V	1.2			V
V_{OH}	I_{OH}= –8mA	2.3V	1.9			V
V_{OH}	I_{OH}= –16mA	3V	2.4			V
V_{OH}	I_{OH}= –24mA	3V	2.3			V
V_{OH}	I_{OH}= –32mA	4.5V	3.8			V
V_{OL}	I_{OL}= 100µA	1.65V to 5.5V			0.1	V
V_{OL}	I_{OL}= 4mA	1.65V			0.45	V
V_{OL}	I_{OL}= 8mA	2.3V			0.3	V
V_{OL}	I_{OL}= 16mA	3V			0.4	V
V_{OL}	I_{OL}= 24mA	3V			0.55	V
V_{OL}	I_{OL}= 32mA	4.5V			0.55	V
I_I	V_I = V_{CC} or GND	V_{CC} = 0V to 5.5 V		±1	±5	µA
I_{off}	V_I or V_O = V_{CC}	V_{CC} = 0V		±1	±10	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	V_{CC} = 1.65V to 5.5 V		1	10	µA
ΔI_{CC}	One input at V_{CC} - 0.6V, other inputs at V_{CC} or GND	3.0V to 5.5V			500	µA
C_I	V_I = V_{CC} or GND	3.3V		7		pF
C_O	V_O = V_{CC} or GND	3.3V		6.3		pF

5.6 Switching Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted). See #i#Parameter Measurement Information

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	V_{CC}	-40°C to 125°C			UNIT
					MIN	TYP	MAX	
t_{pd}	A	Y	C_L = 15pF	1.8V ± 0.15V	1.3		5.5	ns

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted). See #i#Parameter Measurement Information

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	V_{CC}	-40°C to 125°C			UNIT
					MIN	TYP	MAX	
t_{pd}	A	Y	C_L = 15pF	2.5V ± 0.2V	1		4.5	ns
t_{pd}	A	Y	C_L = 50pF	3.3V ± 0.3V	1.1		4.2	ns
t_{pd}	A	Y	C_L = 50pF	5.0V ± 0.5V	1		3.5	ns
C_{pd}			f = 10MHz	1.8V		9		pF
C_{pd}			f = 10MHz	2.5V		11		pF
C_{pd}			f = 10MHz	3.3V		13		pF
C_{pd}			f = 10MHz	5.0V		27		pF

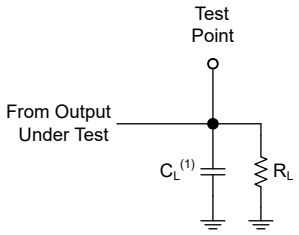
6 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily for the examples listed in the following table. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1MHz, Z_O = 50Ω, t_t ≤ 2.5ns.

The outputs are measured individually with one input transition per measurement.

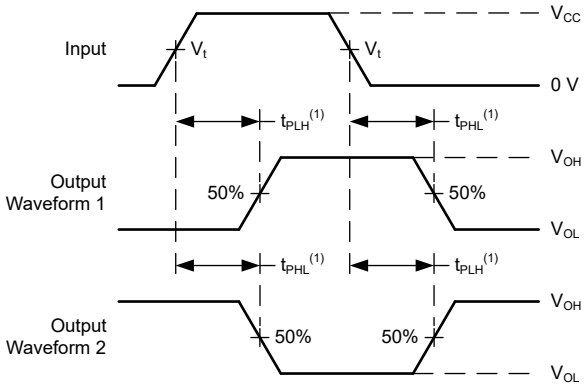
Table 6-1. Push-Pull Outputs

V_{CC}	V_t	R_L	C_L	ΔV
1.8V ± 0.15V	V_{CC}/2	1kΩ	15pF/30pF	0.15V
2.5V ± 0.2V	V_{CC}/2	500Ω	15pF/30pF	0.15V
3.3V ± 0.3V	1.5V	500Ω	15pF/50pF	0.3V
5.0V ± 0.5V	1.5V	500Ω	15pF/50pF	0.3V



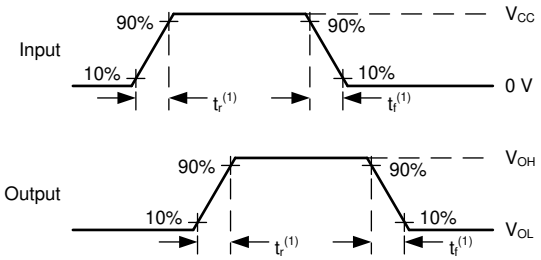
(1) C_L includes probe and test-fixture capacitance.

Figure 6-1. Load Circuit for Push-Pull Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.

Figure 6-2. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t.

Figure 6-3. Voltage Waveforms, Input and Output Transition Times

7 Detailed Description

7.1 Overview

The SN74LVC1GU04-Q1 is a single channel unbuffered CMOS inverter designed with a straightforward single-stage architecture. Unlike multi-stage buffered inverters, unbuffered inverters provide a direct implementation of the logical NOT function with minimal complexity.

The unbuffered design offers versatility in application. While functioning as a standard digital logic gate for conventional switching operations, the device can also operate in the analog linear region. This characteristic makes unbuffered inverters suitable for specialized applications beyond pure digital logic.

Potential applications leveraging the unbuffered architecture include:

- Crystal oscillator circuits
- RC timing networks
- Linear amplification
- Analog signal conditioning

The device provides the fundamental inverter functionality while maintaining the inherent characteristics of unbuffered design, including the natural response curve of a single CMOS stage. This allows system designers flexibility in both digital and analog domains without requiring specialized analog specifications.

7.2 Functional Block Diagram

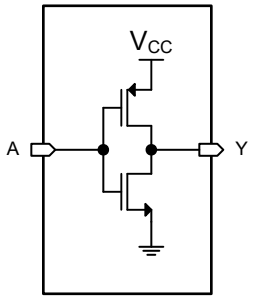


Figure 7-1. Functional Diagram

7.3 Feature Description

7.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important to limit the output power of the device to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs must be left disconnected.

7.3.2 Partial Power Down (I_{off})

This device includes circuitry to disable all outputs when the supply pin is held at 0V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the I_{off} specification in the *Electrical Characteristics* table.

7.3.3 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law (R = V ÷ I).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in *Implications of Slow or Floating CMOS Inputs*.

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a 10kΩ resistor, however, is recommended and will typically meet all requirements.

7.3.4 Clamp Diode Structure

Figure 7-2 shows the inputs and outputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

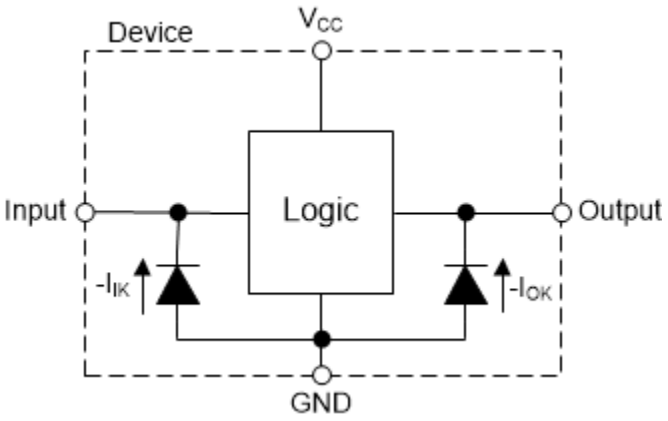


Figure 7-2. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

Table 7-1 lists the functional modes of the SN74LVC1GU04.

Table 7-1. Function Table

INPUT A	OUTPUT Y
H	L
L	H

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The unbuffered inverter is commonly used in oscillator circuits because it is less sensitive to parameter changes in the oscillator circuit due to having lower total gain than an equivalent buffered inverter. An example application circuit is shown in Figure 8-1. To learn more about how to use an unbuffered inverter in an oscillator circuit, refer to the *Use of the CMOS Unbuffered Inverter in Oscillator Circuits* application report.

8.2 Typical Application

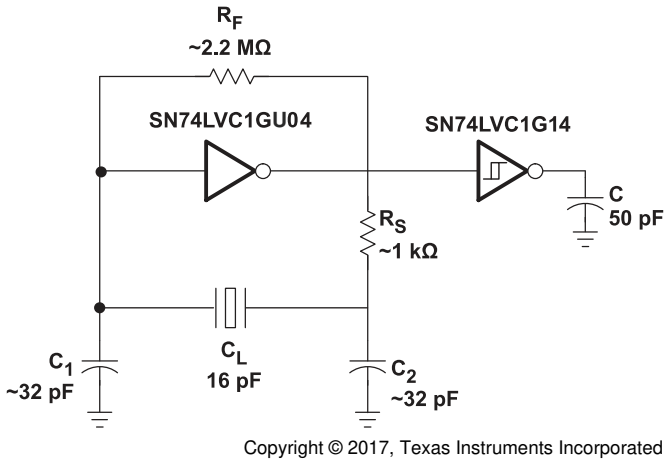


Figure 8-1. Typical Application Diagram

8.2.1 Design Requirements

8.2.1.1 Power Considerations

Ensure that the desired supply voltage is within the range specified in the *Electrical Characteristics*. The supply voltage sets the device electrical characteristics of the device, as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LVC1GU04-Q1 plus the maximum static supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Ensure the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings* is not exceeded.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LVC1GU04-Q1 plus the maximum supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Ensure the maximum total current through GND listed in the *Absolute Maximum Ratings* is not exceeded.

The SN74LVC1GU04-Q1 can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50pF.

The SN74LVC1GU04-Q1 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL}. When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in the *CMOS Power Consumption and Cpd Calculation* application note.

Thermal increase can be calculated using the information provided in the *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices* application note.

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations

Input signals must cross $V_{IL(max)}$ to be considered a logic LOW, and $V_{IH(min)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LVC1GU04-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10kΩ resistor value is often used due to these factors.

The SN74LVC1GU04-Q1 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the Electrical Characteristics table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

8.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Verify that the capacitive load at the output is ≤ 50pF. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74LVC1GU04-Q1 to one or more of the receiving devices.
3. Verify that the resistive load at the output is larger than (V_{CC} / $I_{O(max)}$)Ω. Doing this prevents the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in MΩ; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the *CMOS Power Consumption and Cpd Calculation* application note.

8.2.3 Application Curve

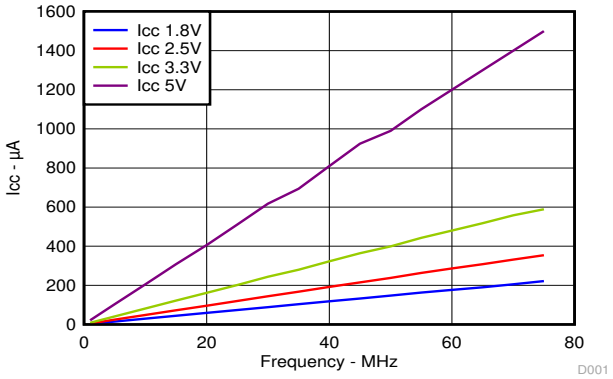


Figure 8-2. I_{CC} vs Frequency

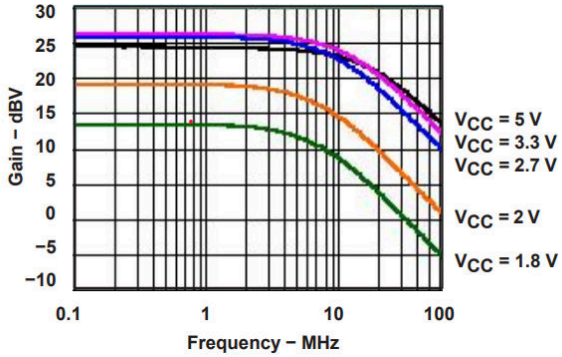


Figure 8-3. Open-Loop Gain Characteristics

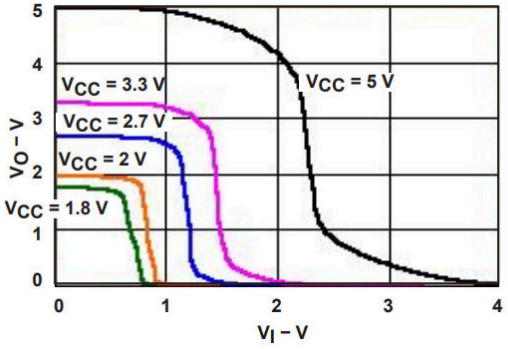


Figure 8-4. V_O vs V_I Characteristics

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions*.

Verify that each V_{CC} terminal has a good bypass capacitor to prevent power disturbance. For the SN74LVC1GU04-Q1, a 0.1µF bypass capacitor is recommended. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1µF and 1µF are commonly used in parallel.

8.4 Layout

8.4.1 Layout Guidelines

- Bypass capacitor placement
  - Place near the positive supply terminal of the device
  - Provide an electrically short ground return path
  - Use wide traces to minimize impedance
  - Keep the device, capacitors, and traces on the same side of the board whenever possible
- Signal trace geometry
  - 8mil to 12mil trace width
  - Lengths less than 12cm to minimize transmission line effects
  - Avoid 90° corners for signal traces
  - Use an unbroken ground plane below signal traces
  - Flood fill areas around signal traces with ground
  - Parallel traces must be separated by at least 3x dielectric thickness
  - For traces longer than 12cm
    - Use impedance controlled traces
    - Source-terminate using a series damping resistor near the output
    - Avoid branches; buffer each signal that must branch separately

8.4.2 Layout Example

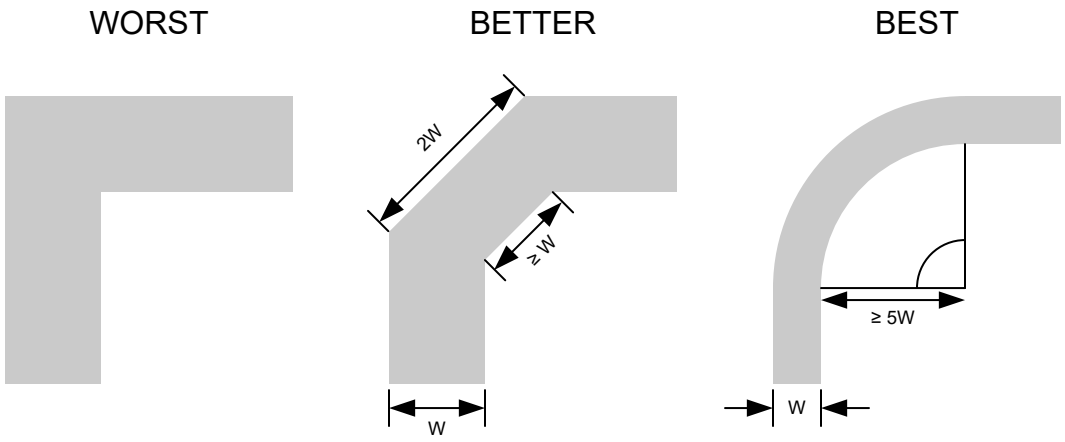


Figure 8-5. Example Trace Corners for Improved Signal Integrity

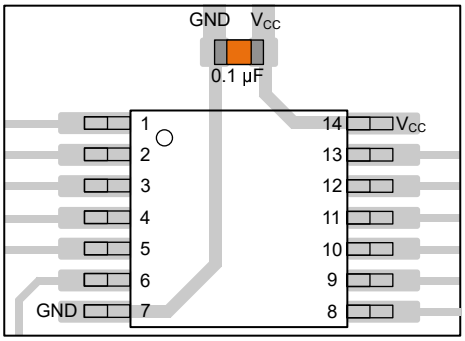


Figure 8-6. Example Bypass Capacitor Placement for TSSOP and Similar Packages

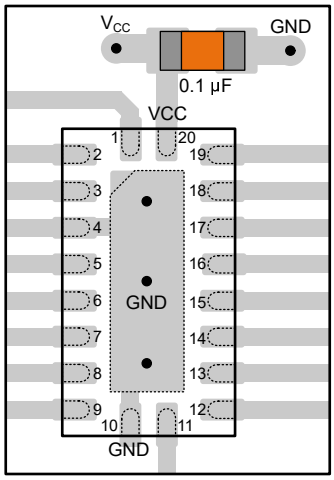


Figure 8-7. Example Bypass Capacitor Placement for WQFN and Similar Packages

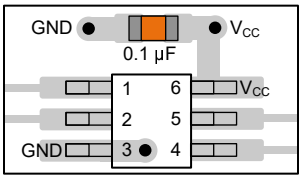


Figure 8-8. Example Bypass Capacitor Placement for SOT, SC70 and Similar Packages

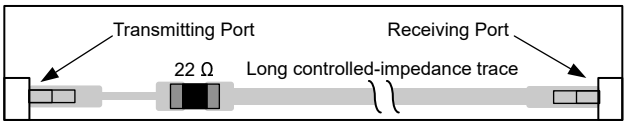


Figure 8-9. Example Damping Resistor Placement for Improved Signal Integrity

9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *CMOS Power Consumption and C_{pd} Calculation* application note
- Texas Instruments, *Designing With Logic* application note
- Texas Instruments, *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices* application note

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
All trademarks are the property of their respective owners.

9.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

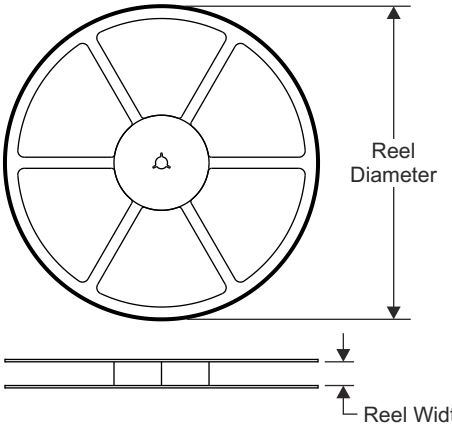
Changes from Revision * (October 2025) to Revision A (November 2025)	Page
• Changed the document status from Advanced Information to Production Data	1
• Updated the numbering format for tables, figures, and cross-references throughout the document	1

11 Mechanical, Packaging, and Orderable Information

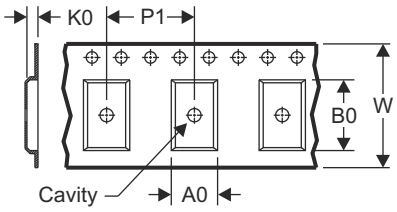
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

11.1 Tape and Reel Information

REEL DIMENSIONS

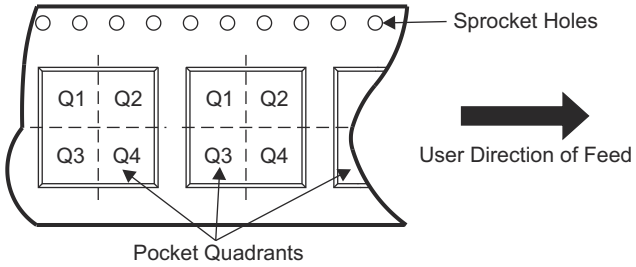


TAPE DIMENSIONS



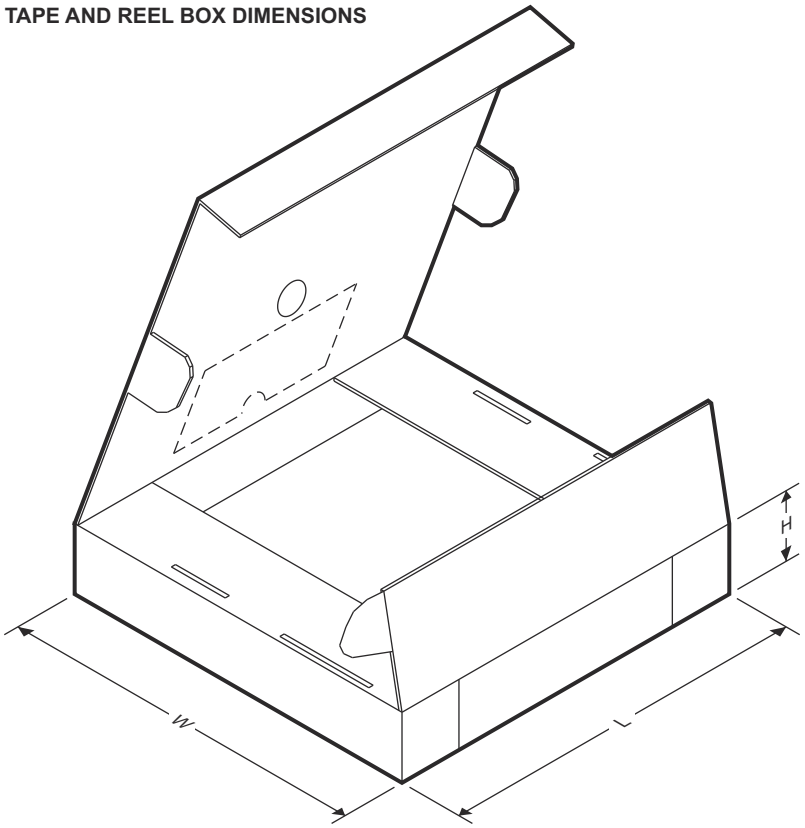
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1GU04-Q1	SC70	DCK	5	3000	180	8.4	2.30	2.50	1.20	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1GU04-Q1	SC70	DCK	5	3000	210	185	35

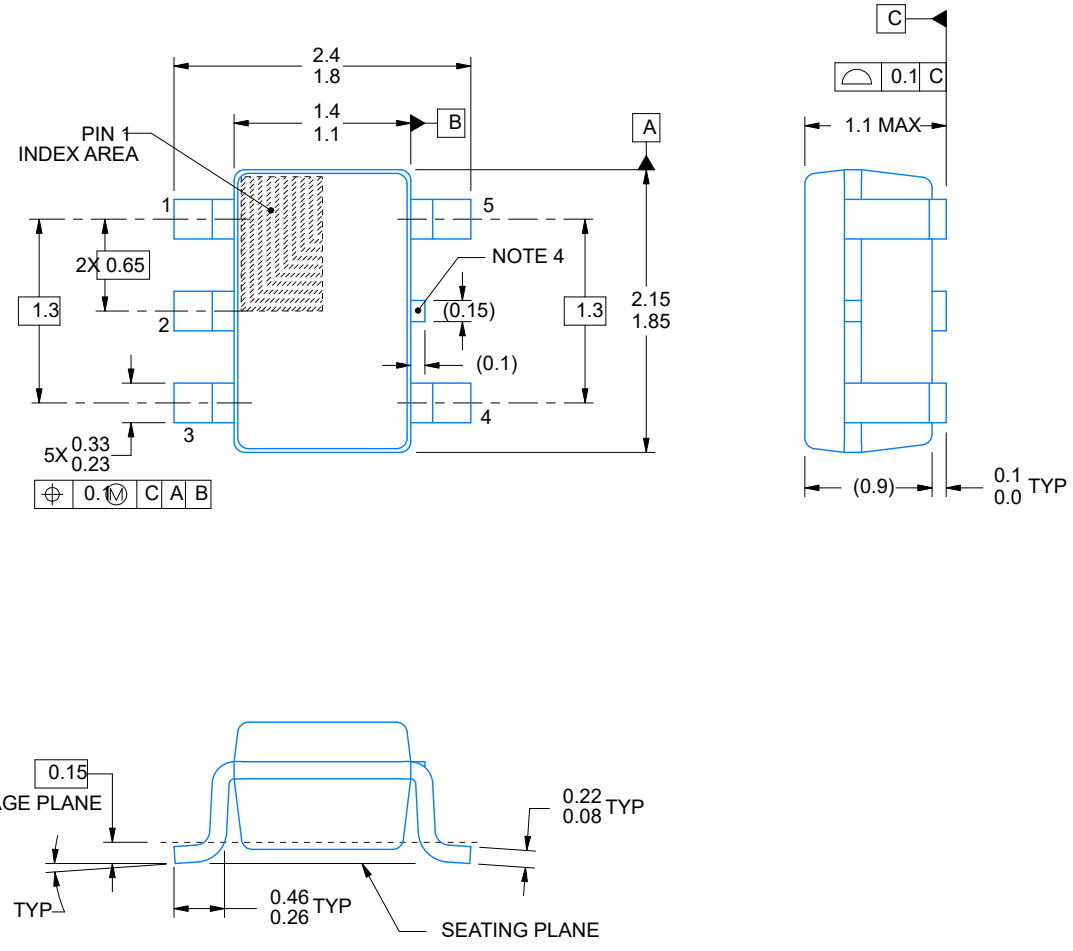
11.2 Mechanical Data

PACKAGE OUTLINE

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



4214834/C 03/2023

NOTES:

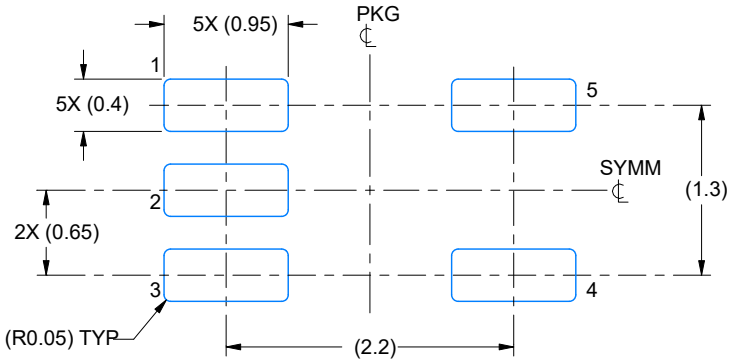
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dim ensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-203.
4. Support pin may differ or may not be present.

EXAMPLE BOARD LAYOUT

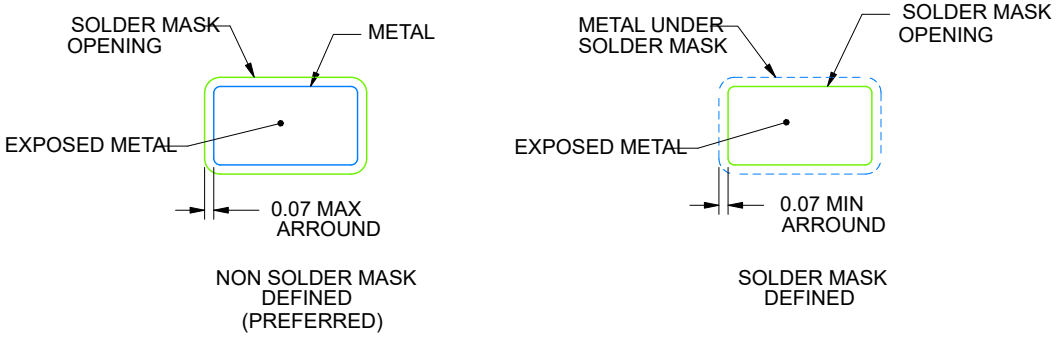
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

4214834/C 03/2023

NOTES: (continued)

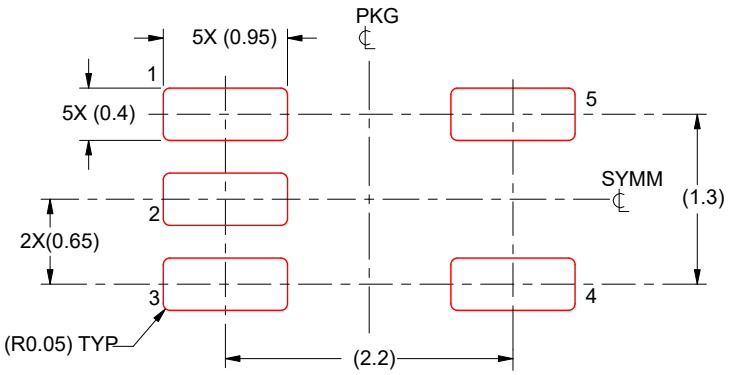
4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214834/C 03/2023

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
PCLVC1GU04DCKRQ1	Active	Preproduction	SC70 (DCK) | 5	3000 | LARGE T&R	-	Call TI	Call TI	-40 to 125	
SN74LVC1GU04DCKRQ1	Active	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	22G

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

OTHER QUALIFIED VERSIONS OF SN74LVC1GU04-Q1 :

- Catalog : SN74LVC1GU04

NOTE: Qualified Version Definitions:

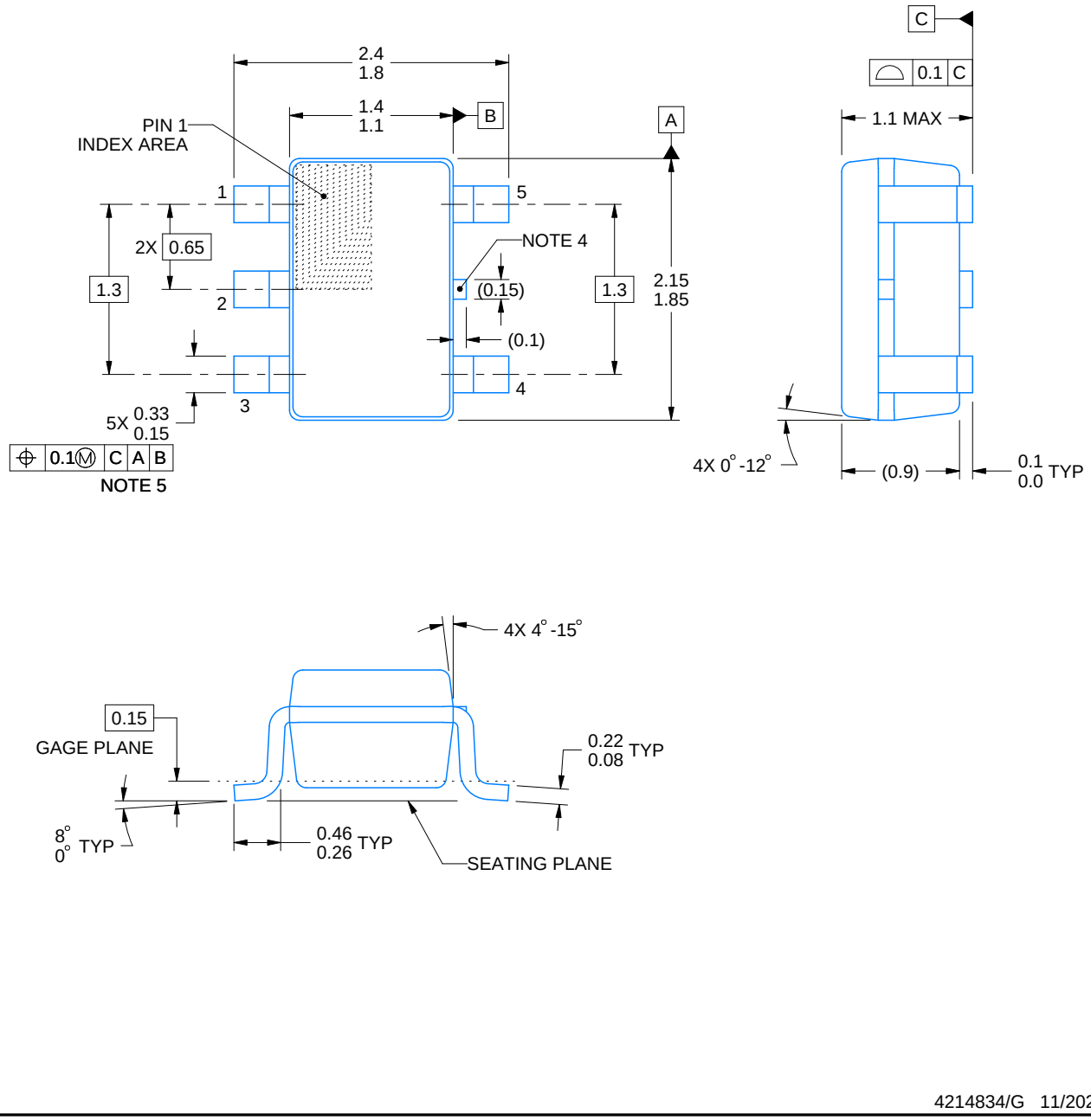
- Catalog - TI's standard catalog product

PACKAGE OUTLINE

DCK0005A

SOT - 1.1 max height

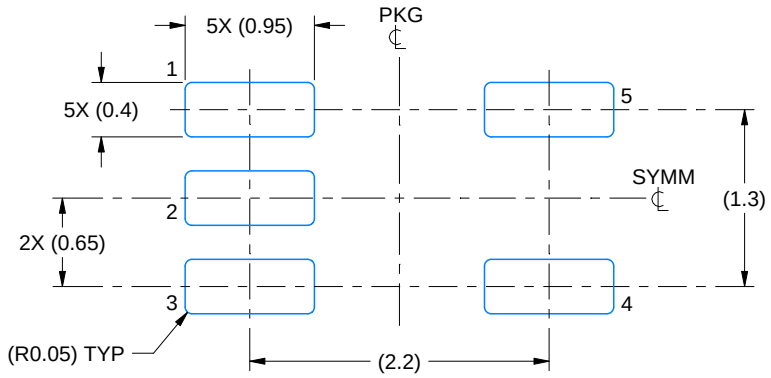
SMALL OUTLINE TRANSISTOR



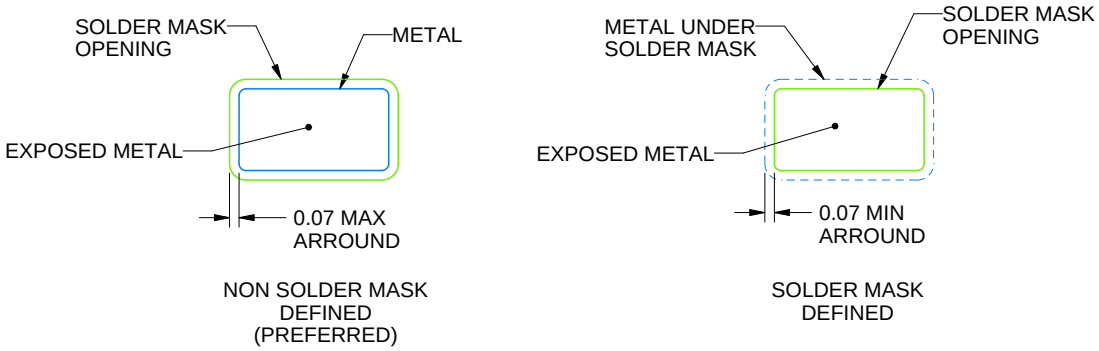
4214834/G 11/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

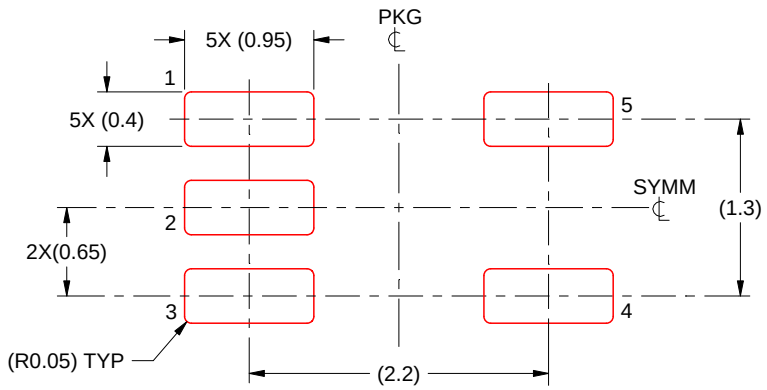


SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI’s products are provided subject to TI’s Terms of Sale, TI’s General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI’s provision of these resources does not expand or otherwise alter TI’s applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Last updated 10/2025